

Darlington Transistor TO-3



Description:

Darlington complementary silicon power transistors. Designed for general-purpose amplifier and low frequency switching applications.

Features:

- High DC current gain - $h_{FE} = 3,500$ (typical) at $I_C = 5A$ DC
- Collector-emitter sustaining voltage - at 100mA
 V_{CEO} (sus) = 80V DC (min.) - 2N6058
- Monolithic construction with built-in-base-emitter shunt resistors

Maximum Ratings

Characteristic	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	V DC
Collector-Base Voltage	V_{CB}		
Emitter-Base Voltage	V_{EB}		
Collector Current -Continuous -Peak	I_C	12 20	A DC
Base Current	I_B	0.2	
Total Power Dissipation at $T_C = 25^\circ C$ Derate above $25^\circ C$	P_D	150 0.857	W W/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{Stg}	-65 $^\circ C$ to +200 $^\circ C$	$^\circ C$

Thermal Characteristics

Characteristic	Symbol	Max.	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	1.17	$^\circ C/W$

(1) Indicates JEDEC Registered Data.

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Electrical Characteristics (TC = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
Off Characteristics				
Collector-Emitter Sustaining Voltage (2) (I _C = 100mA DC, I _B = 0)	V _{CEO (sus)}	80	-	V DC
Collector Cut off Current (V _{CE} = 40V DC, I _B = 0)	I _{CEO}	-	1	mA DC
Collector Cut off Current (V _{CE} = Rated V _{CEO} , V _{BE (off)} = 1.5V DC) (V _{CE} = Rated V _{CEO} , V _{BE (off)} = 1.5V DC, T _C = 150°C)	I _{CEx}	-	0.5 5	
Emitter Cut off Current (V _{BE} = 5V DC, I _C = 0)	I _{EBO}	-	2	

On Characteristics (2)

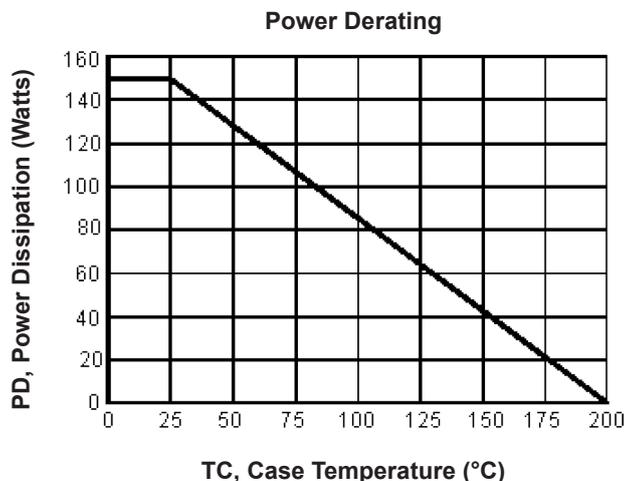
DC Current Gain (I _C = 6A DC, V _{CE} = 3V DC) (I _C = 12A DC, V _{CE} = 3V DC)	h _{FE}	750 100	18,000 -	-
Collector-Emitter Saturation Voltage (I _C = 6A DC, I _B = 24mA DC) (I _C = 12A DC, I _B = 120mA DC)	V _{CE (sat)}	- -	2 3	V DC
Base-Emitter Saturation Voltage (I _C = 12A DC, I _B = 120mA DC)	V _{BE (sat)}	-	4	
Base-Emitter On Voltage (I _C = 6A DC, V _{CE} = 3V DC)	V _{BE (on)}	-	2.8	

Dynamic Characteristics

Magnitude of Common-Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio (I _C = 5A DC, V _{CE} = 3V DC, f = 1MHz)	h _{fe}	4	-	MHz
Output Capacitance (V _{CB} = 10V DC, I _E = 0, f = 0.1MHz)	C _{ob}	-	500 300	pF
Small-Signal Current Gain (I _C = 5A DC, V _{CE} = 3V DC, f = 1kHz)	h _{fe}	300	-	-

Indicates JEDEC Registered Data.

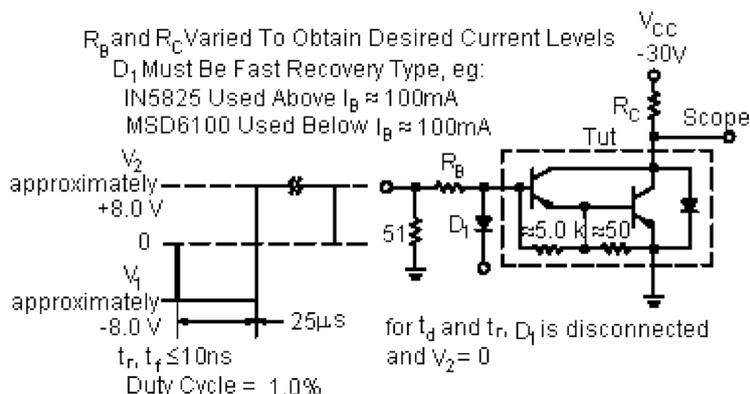
(2) Pulse test: Pulse Width = 300µs, Duty Cycle = 2%.



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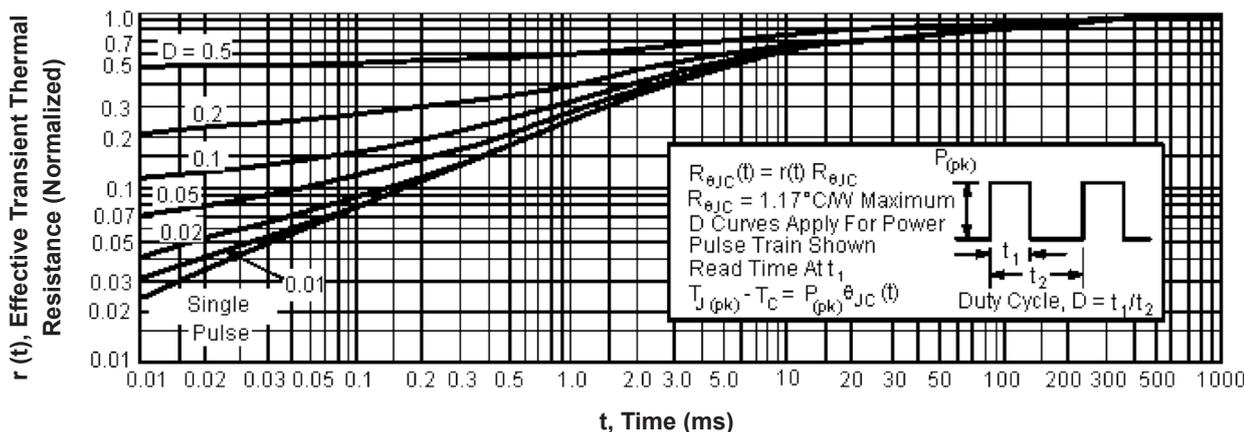


Switching Times Test Circuit

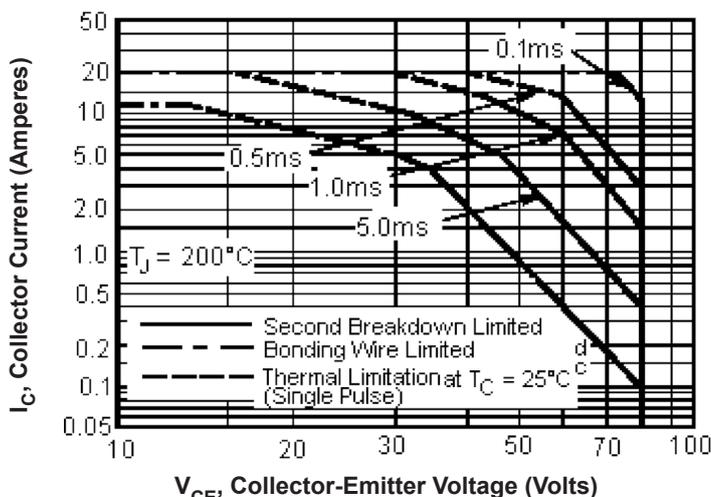


For NPN Test Circuit Reverse Diode and Voltage Polarities

Thermal Response



Active-Region Safe Operating Area



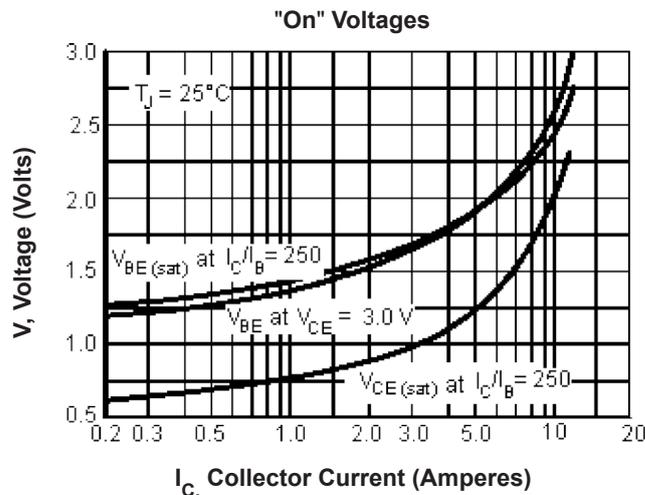
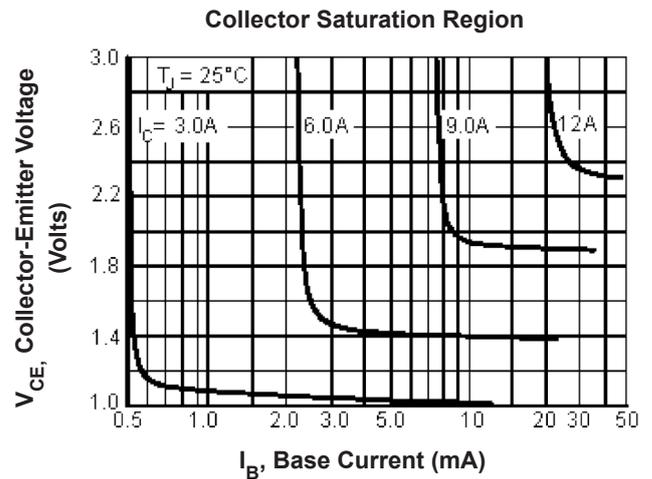
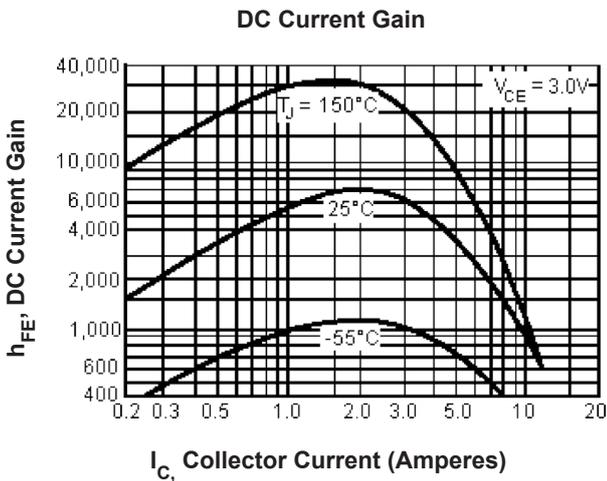
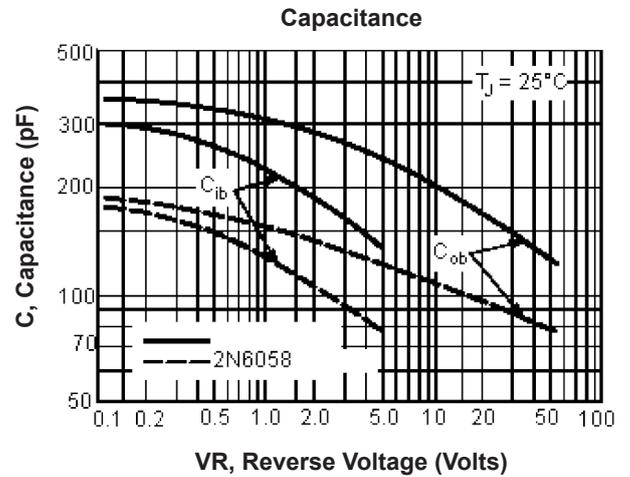
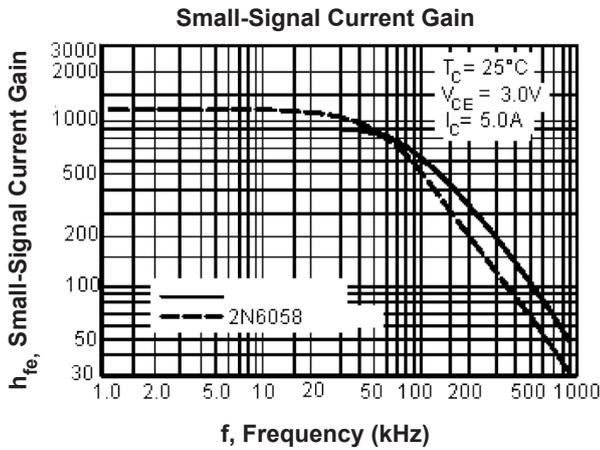
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data is based on $T_{J(pk)} = 200^\circ\text{C}$; TC is variable depending on conditions. Second breakdown pulse limits are valid for duty

cycles to 10% provided $T_{J(pk)} \leq 200^\circ\text{C}$; $T_{J(pk)}$ may be calculated from the data. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



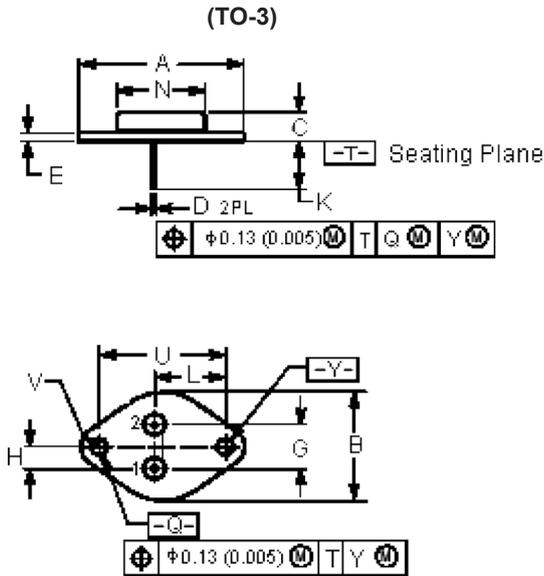
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Dimensions



Dimensions	Min.	Max.
A	1.55 (39.37)	Reference
B	-	1.05 (26.67)
C	0.25 (6.35)	0.335 (8.51)
D	0.038 (0.97)	0.043 (1.09)
E	0.055 (1.4)	0.07 (1.77)
G	0.43 (10.92) BSC	
H	0.215 (5.46) BSC	
K	0.44 (11.18)	0.48 (12.19)
L	0.665 (16.89) BSC	
N	-	0.83 (21.08)
Q	0.151 (3.84)	0.165 (4.19)
U	1.187 (30.15) BSC	
V	0.131 (3.33)	0.188 (4.77)

Dimensions : Inches (Millimetres)

Pin Configuration:

- Pin 1. Base
- 2. Emitter
- Collector (Case)

Part Number Table

Description	Part Number
Darlington Transistor, TO-3	2N6058

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